

AMENDMENT

Please amend the application as indicated hereafter.

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In the Claims :

Claims 1-10 (canceled).

10 11. (original) An interconnect structure, comprising:
a first dielectric layer;
a conducting line disposed on said first dielectric layer;
a first liner layer disposed on surfaces of said first dielectric layer and said
conducting line;

15 a second liner layer disposed on a surface of said first liner; and
a second dielectric layer covering said second liner, said second dielectric
layer comprising a contact widow opening therein through said second liner layer and said
first liner layer to expose the surface of said conducting line.

12. (original) The interconnect structure of claim 11, wherein said
20 conducting line is formed by stacking a first barrier layer, an Al-dominated metal layer,
and a second barrier layer.

13. (original) The interconnect structure of claim 12, wherein each of
said first barrier and second barrier layers is a TiN layer or a stacked layer comprising a
TiN layer and a Ti layer.

25 14. (original) The interconnect structure of claim 11, wherein
materials of said first liner layer and said second dielectric layer are the same.

15. (original) The interconnect structure of claim 11, wherein an etch

selectivity ratio of said second dielectric layer to said second liner is between 50 and 70.

16. (original) The interconnect structure of claim 11, wherein said second dielectric layer includes silicon oxide.

17. (original) The interconnect structure of claim 11, wherein said 5 second liner layer is SiN_x or SiON .

18. (original) The interconnect structure of claim 11 further comprising a contact window in said first dielectric layer, said contact window being electrically connected to said conducting line.

19. (original) The interconnect structure of claim 11, further comprising a conducting layer filled into said contact window opening.